

WHAT IS CLAIMED IS:

1. A semiconductor laser device comprising:

a GaAs substrate;

an InGaAsP quantum well active layer supported on
5 the GaAs substrate, said quantum well active layer being
composed of one or a plurality of well layers and a
plurality of barrier layers alternately disposed;

an n-type cladding layer and a p-type cladding
layer, which are provided in a manner so as to interpose
10 the quantum well active layer therebetween;

a first guide layer provided between the n-type
cladding layer and the quantum well active layer; and

a second guide layer provided between the p-type
cladding layer and the quantum well active layer,

15 wherein said semiconductor laser device has an
oscillation wavelength of larger than 760 nm and smaller
than 800 nm, and

the first guide layer is formed of InGaP.

20 2. The semiconductor laser device according to claim
1, wherein the second guide layer is formed of AlGaAs.

3. The semiconductor laser device according to claim
1, wherein the first guide layer has a thickness of 30 Å or
25 more.

4. The semiconductor laser device according to claim 1, wherein the first guide layer has a composition being lattice-matched with the GaAs substrate or having a compressive strain or a tensile strain of not more than 1% with respect to the GaAs substrate.

5. The semiconductor laser device according to claim 1, wherein an Al mole fraction of the second guide layer is 0.2 or more.

6. The semiconductor laser device according to claim 1, wherein a luminous shape stabilizer guide layer formed of AlGaAs is provided between the first guide layer and the n-type cladding layer.

7. The semiconductor laser device according to claim 6, wherein an Al mole fraction of the luminous shape stabilizer guide layer is 0.2 or more.

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8. The semiconductor laser device according to claim 1, wherein the one or each well layer has a compressive strain.

9. The semiconductor laser device according to claim 8, wherein a quantity of the compressive strain is not more than 3.5%.

5 10. The semiconductor laser device according to claim 1, wherein the barrier layers have a tensile strain.

10 11. The semiconductor laser device according to claim 10, wherein a quantity of the tensile strain is not more than 3.5%.

12. An optical disc unit wherein the semiconductor laser device of claim 1 is used.